NEGATIVE CAPACITANCE TOPOLOGICAL QUANTUM FIELD-EFFECT TRANSISTOR

Abstract

Disclosed herein is a structure comprising: a top gate electrode and a bottom gate electrode, a channel layer formed from a channel material with a band gap modulable by electric field, the channel layer being electrically insulated from the top gate electrode and the bottom gate electrode and being located adjacent to at least one layer of a negative capacitance material.

Fig. 1